



DESCRIPTION

The **SD012-121-011** is a high sensitivity, low capacitance and noise, 0.3mm diameter active area InGaAs photodiode, sensitive to wavelengths in visible extended (450-1700nm) spectral range and used for sensing applications. The photodetector is assembled in a TO-46 package.

FEATURES

- Low Noise
- Low Dark Current and Capacitance
- High Sensitivity
- Light Detection (Visible, NIR, SWIR)

RELIABILITY

This high-reliability device is in principle able to meet military test requirements (Mil-STD-750, Mil-STD-883) after proper screening and group test. Contact Luna Optoelectronics for recommendations on specific test conditions and procedures.

APPLICATIONS

- Industrial Sensing
- Security and Defense
- Communication

ABSOLUTE MAXIMUM RATINGS

SYMBOL	MIN	MAX	UNITS	
Reverse Voltage		20	V	$T_a = 23^\circ\text{C}$
Operating Temperature	0 to	+85	$^\circ\text{C}$	
Storage Temperature	-25 to	+85	$^\circ\text{C}$	
Soldering Temperature*		+260	$^\circ\text{C}$	> 2mm from case for < 5 sec
Wavelength Range	400 to	1700	nm	

Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.

OPTO-ELECTRICAL PARAMETERS

T_a = 23°C unless noted otherwise

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Breakdown Voltage	I _{bias} = 100 μA	10	-	-	V
Responsivity	λ = 600 nm	0.3	0.35	-	A/W
Responsivity	λ = 1200 nm	0.7	0.85	-	A/W
Responsivity	λ = 1550 nm	0.9	1.00	-	A/W
Shunt Resistance	V _{bias} = 10 mV	5	30	-	MΩ
Dark Current	V _{bias} = 1V	-	2	20	nA
Capacitance	V _{bias} = 1V; f = 1MHz	-	6	20	pF
Rise Time (50Ω load)	V _{bias} = 5V; λ = 826 nm	-	5	-	ns
Noise Equivalent Power	λ = 900nm	-	1.0	-	10 ⁻¹³ W/Hz ^{0.5}

TYPICAL PERFORMANCE

SPECTRAL RESPONSE

